

Silicon Transistors

	Type No.	Case	Construction (see note 1)	Maximum Ratings at 25°C amb.					Characteristics									SPECIAL FEATURES
				V _{CB} V	V _{CE} V	V _{EB} V	I _C A	P _{tot} W	h _{FE}			f _T		V _{CE(SAT)}				
									I _C mA	Min.	Max.	I _C mA	Min. Mc/s	I _C mA	I _B mA	Max. V		
NPN Microwave Power Source	TIXS12	ZZ	PE	30	15	2	0.2	1.0	50	20	200	50	1500†	—	—	—	Po > 250 mW at 1.5 Gc Po > 125 mW at 1.5 Gc	
	TIXS13	ZZ	PE	30	15	2	0.2	1.0	50	20	200	50	1200†	—	—	—		
NPN Medium Power High Voltage	2N696	TO5	P	60	40	5	0.5	0.6	150	20	60	50	40	150	15	1.5	Complementary to 2N1131 Complementary to 2N1132	
	2N697	TO5	P	60	40	5	0.5	0.6	150	40	120	50	50	150	15	1.5		
	2N698	TO5	P	120	80	7	0.5	0.8	150	20	60	50	40	150	15	5.0	Total switching time < 30ns	
	2N1507	TO5	P	60	30	5	1.0	0.8	150	100	300	50	50	150	15	1.5		
	2N1613	TO5	P	75	50	7	0.5	0.8	150	40	120	50	60	150	15	1.5		
	2N1711	TO5	P	75	50	7	1.0	0.8	150	100	300	50	70	150	15	1.5		
	2N1889	TO5	P	100	60	7	0.5	0.8	150	40	120	50	50	150	15	5.0		
	2N1890	TO5	P	100	60	7	0.5	0.8	150	100	300	50	60	150	15	5.0		
	2N1893	TO5	P	120	80	7	0.5	0.8	150	40	120	50	50	150	15	5.0		
	2N2192	TO5	PE	60	40	5	1.0	0.8	150	100	300	50	50	150	15	0.35		
	2N2192A	TO5	PE	60	40	5	1.0	0.8	150	100	300	50	50	150	15	0.25		
	2N2193	TO5	PE	80	50	8	1.0	0.8	150	40	120	50	50	150	15	0.35		
	2N2193A	TO5	PE	80	50	8	1.0	0.8	150	40	120	50	50	150	15	0.25		
	2N2194	TO5	PE	60	40	5	1.0	0.8	150	20	60	50	50	150	15	0.35		
	2N2194A	TO5	PE	60	40	5	1.0	0.8	150	20	60	50	50	150	15	0.25		
	2N2243	TO5	PE	120	80	7	1.0	0.8	150	40	120	50	50	150	15	0.35		
	2N2243A	TO5	PE	120	80	7	1.0	0.8	150	40	120	50	50	150	15	0.25		
	2N3036	TO5	PE	120	80	7	1.2	0.8	150	50	150	10	50	150	15	0.25		
	2N3418	TO5	PE	85	60	8	3	0.8	1000	20	60	100	40	1A	100	0.25		Ptot at 100°C case temp 10W
	2N3419	TO5	PE	125	80	8	3	0.8	1000	20	60	100	40	1A	100	0.25		
2N3420	TO5	PE	85	60	8	3	0.8	1000	40	120	100	40	1A	100	0.25			
2N3421	TO5	PE	125	80	8	3	0.8	1000	40	120	100	40	1A	100	0.25			
PNP Medium Power Amplifiers Switches	2N1131	TO5	P	-50	-35	-5	0.60	0.60	-150	20	45	-50	50	-150	-15	-1.5	Complementary to 2N696 Complementary to 2N697	
	2N1132	TO5	P	-50	-35	-5	0.60	0.60	-150	30	90	-50	60	-150	-15	-1.5		
	2N2695	TO46	PE	-25	-25	-5	0.50	0.36	-50	30	130	-50	100	-300	-30	-1.0		
	2N2696	TO18	PE	-25	-25	-5	0.50	0.36	-50	30	130	-50	100	-300	-30	-1.0		
	2N2904	TO5	PE	-60	-40	-5	0.6	0.6	-150	40	120	-50	200	-150	15	0.4		
	2N2904A	TO5	PE	-60	-60	-5	0.6	0.6	-150	40	120	-50	200	-150	15	0.4		
	2N2905	TO5	PE	-60	-40	-5	0.6	0.6	-150	100	300	-50	200	-150	15	0.4		
	2N2905A	TO5	PE	-60	-60	-5	0.6	0.6	-150	100	300	-50	200	-150	15	0.4		
	2N2906	TO18	PE	-60	-40	-5	0.6	0.4	-150	40	120	-50	200	-150	15	0.4		
	2N2906A	TO18	PE	-60	-60	-5	0.6	0.4	-150	40	120	-50	200	-150	15	0.4		
	2N2907	TO18	PE	-60	-40	-5	0.6	0.4	-150	100	300	-50	200	-150	15	0.4		
	2N2907A	TO18	PE	-60	-60	-5	0.6	0.4	-150	100	300	-50	200	-150	15	0.4		
	2N3702	Silect	PE	-40	-25	-5	0.2	0.3	-50	60	300	-50	100	-50	-5	-0.25		
2N3703	Silect	PE	-50	-30	-5	0.2	0.3	-50	30	150	-50	100	-50	-5	-0.25			
Complementary Medium Power Amplifiers	TIS60	Silect	PE	40	25	5	0.4	0.3	50	100	300	—	—	100	5	0.6	N.P.N. N.P.N. P.N.P. P.N.P.	
	TIS60M	Silect	PE	40	25	5	0.4	0.3	50	100	300	—	—	100	5	0.6		
	TIS61	Silect	PE	-40	-25	-5	0.4	0.3	-50	100	300	—	—	-50	-5	-0.25		
	TIS61M	Silect	PE	-40	-25	-5	0.4	0.3	-50	100	300	—	—	-50	-5	-0.25		
NPN High Speed Core Drivers	2N3830	TO5	PE	80	50	5	1.2	1.0	500	30	—	50	200	500	50	0.5	Storage time < 40ns at 1 Amp	
	2N3831	TO5	PE	70	40	5	1.2	1.0	500	35	—	50	200	500	50	0.5		

NOTE 1: The following symbols have been used throughout the Product Summary:

Under "Construction":

A — Alloyed
D — Diffused
E — Epitaxial
G — Grown
M — Mesa
P — Planar

Under h_{FE}:

* — h_{fe}

Under f_T:

φ — f_{hfb}
Δ — f_{hfe}
‡ — typical

Under Dissipation:

† — dissipation at T_{case} = 25°C